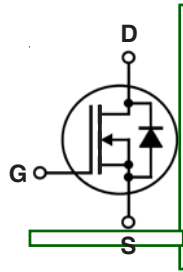


High Voltage Depletion Mode Power MOSFET

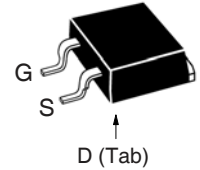
IXTA1R6N100D2HV

$V_{DSX} = 1000V$
 $I_{D(on)} \geq 1.6A$
 $R_{DS(on)} \leq 10\Omega$

N-Channel



TO-263HV
(IXTA..HV)



G = Gate D = Drain
S = Source Tab = Drain

| Symbol | Test Conditions | Maximum Ratings | |
|------------|--|-------------------|------------|
| V_{DSX} | $T_J = 25^\circ C$ to $150^\circ C$ | 1000 | V |
| V_{GSX} | Continuous | ± 20 | V |
| V_{GSM} | Transient | ± 30 | V |
| P_D | $T_C = 25^\circ C$ | 100 | W |
| T_J | | - 55 ... +150 | $^\circ C$ |
| T_{JM} | | 150 | $^\circ C$ |
| T_{stg} | | - 55 ... +150 | $^\circ C$ |
| T_L | Maximum Lead Temperature for Soldering | 300 | $^\circ C$ |
| T_{SOLD} | 1.6 mm (0.062in.) from Case for 10s | 260 | $^\circ C$ |
| M_d | Mounting Force | 10.65 / 2.2..14.6 | N/lb |
| Weight | | 2.5 | g |

Features

- High Voltage package
- High Blocking Voltage
- Normally ON Mode
- International Standard Package
- Molding Epoxies Meet UL94 V-0 Flammability Classification

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Audio Amplifiers
- Start-Up Circuits
- Protection Circuits
- Ramp Generators
- Current Regulators
- Active Loads

| Symbol | Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified) | Characteristic Values | | |
|----------------|---|-----------------------|------|-------------------------|
| | | Min. | Typ. | Max. |
| BV_{DSX} | $V_{GS} = -5V, I_D = 250\mu A$ | 1000 | | V |
| $V_{GS(off)}$ | $V_{DS} = 25V, I_D = 100\mu A$ | - 2.5 | | - 4.5 V |
| I_{GSX} | $V_{GS} = \pm 20V, V_{DS} = 0V$ | | | ± 100 nA |
| $I_{DSX(off)}$ | $V_{DS} = V_{DSX}, V_{GS} = -5V$ $T_J = 125^\circ C$ | | | 2 μA 25 μA |
| $R_{DS(on)}$ | $V_{GS} = 0V, I_D = 0.8A, \text{ Note 1}$ | | | 10 Ω |
| $I_{D(on)}$ | $V_{GS} = 0V, V_{DS} = 50V, \text{ Note 1}$ | 1.6 | | A |

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|-------------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 30\text{V}$, $I_D = 0.8\text{A}$, Note 1 | 0.65 | 1.10 | S |
| C_{iss} | $V_{GS} = -10\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$ | | 645 | pF |
| C_{oss} | | | 43 | pF |
| C_{rss} | | | 11 | pF |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = \pm 5\text{V}$, $V_{DS} = 500\text{V}$, $I_D = 0.8\text{A}$ $R_G = 5\Omega$ (External) | | 27 | ns |
| t_r | | | 65 | ns |
| $t_{d(off)}$ | | | 34 | ns |
| t_f | | | 41 | ns |
| $Q_{g(on)}$ | $V_{GS} = 5\text{V}$, $V_{DS} = 500\text{V}$, $I_D = 0.8\text{A}$ | | 27.0 | nC |
| Q_{gs} | | | 1.6 | nC |
| Q_{gd} | | | 13.5 | nC |
| R_{thJC} | | | | 1.25 $^\circ\text{C/W}$ |

Safe-Operating-Area Specification

| Symbol | Test Conditions | Characteristic Values | | |
|--------|---|-----------------------|------|------|
| | | Min. | Typ. | Max. |
| SOA | $V_{DS} = 800\text{V}$, $I_D = 75\text{mA}$, $T_C = 75^\circ\text{C}$, $T_p = 5\text{s}$ | 60 | | W |

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|----------|--|-----------------------|------|---------------|
| | | Min. | Typ. | Max. |
| V_{SD} | $I_F = 1.6\text{A}$, $V_{GS} = -10\text{V}$, Note 1 | | 0.8 | 1.3 V |
| t_{rr} | $I_F = 1.6\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$, $V_{GS} = -10\text{V}$ | | 970 | ns |
| I_{RM} | | | 9.96 | A |
| Q_{RM} | | | 4.80 | μC |

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

| | | | | | | | | | |
|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

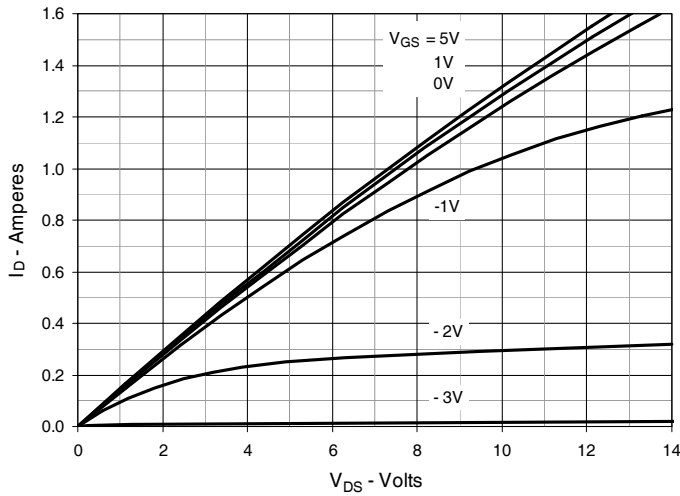
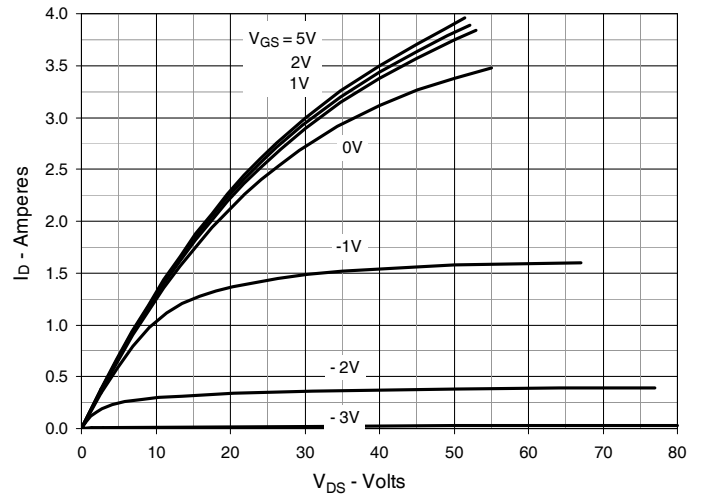
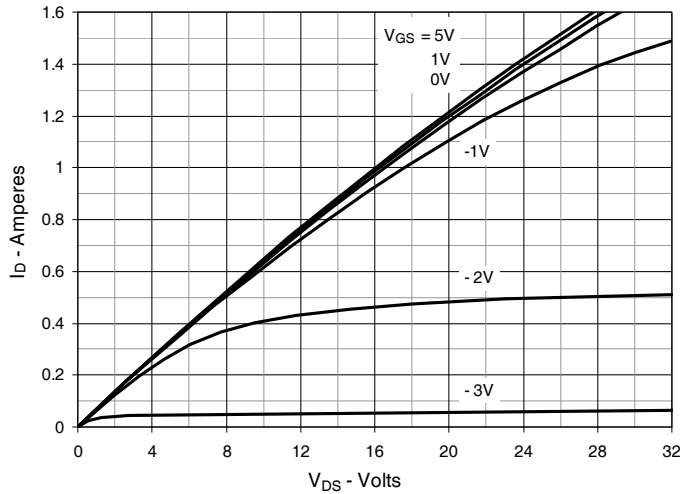
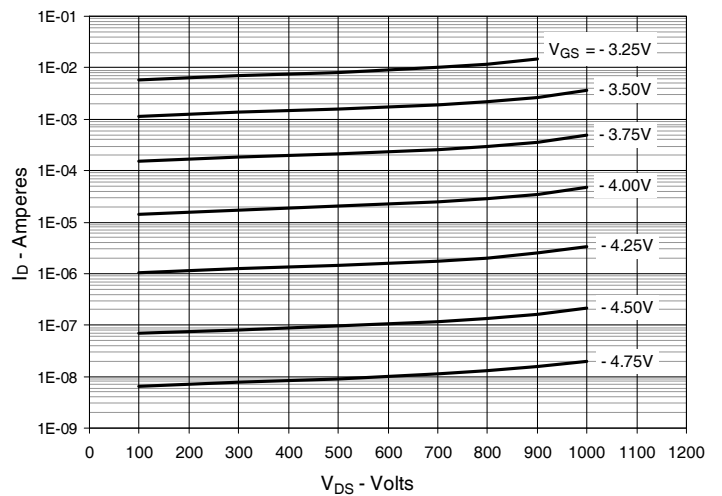
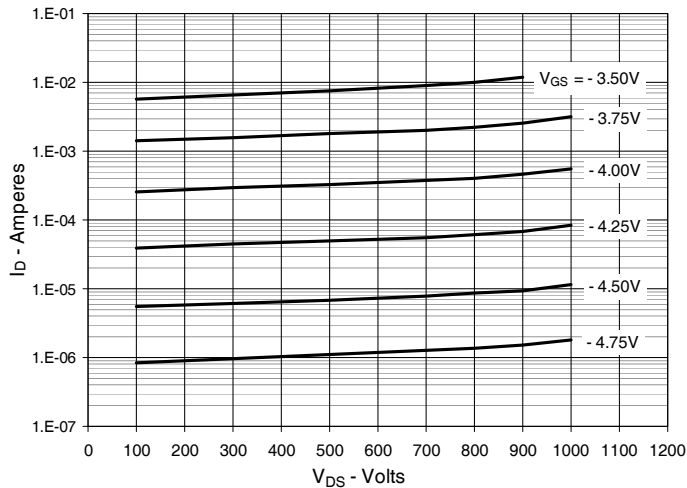
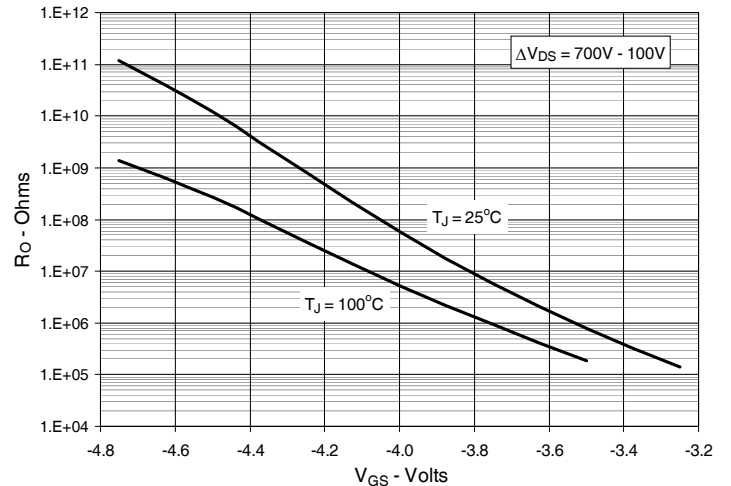
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 4. Drain Current @ $T_J = 25^\circ\text{C}$

Fig. 5. Drain Current @ $T_J = 100^\circ\text{C}$

Fig. 6. Dynamic Resistance vs. Gate Voltage


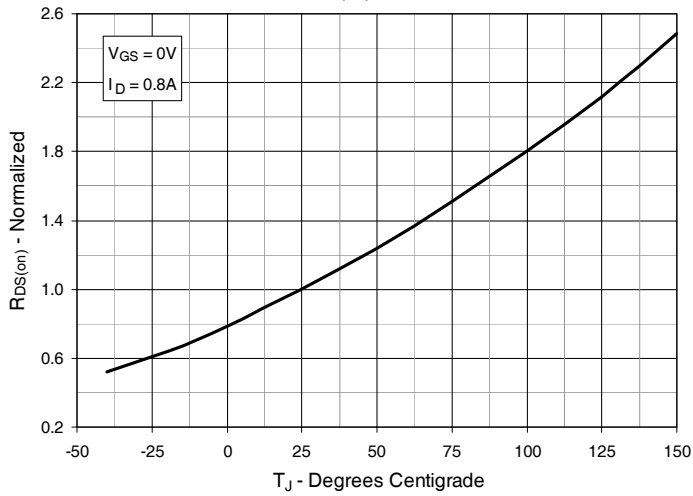
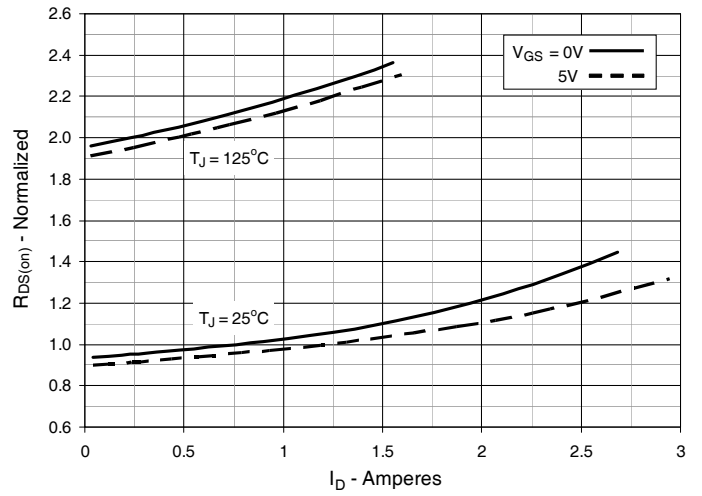
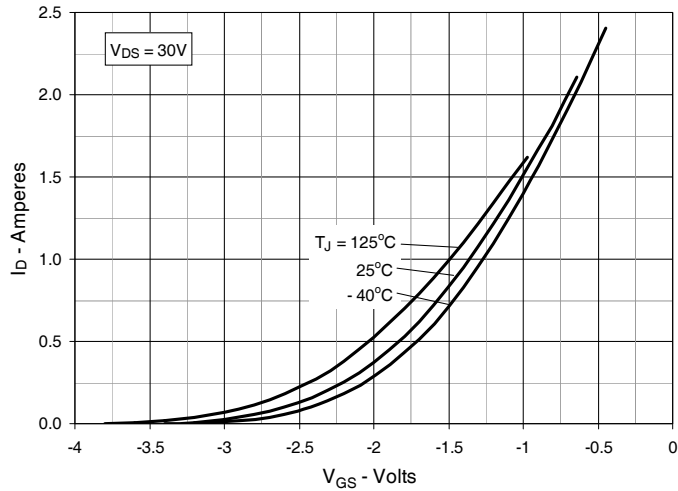
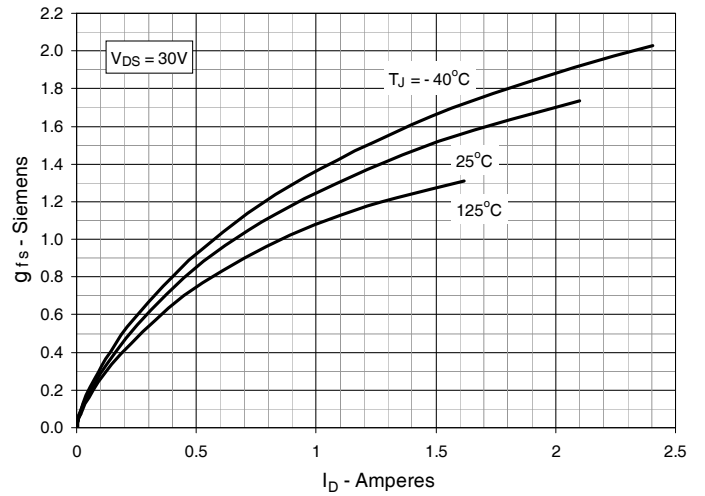
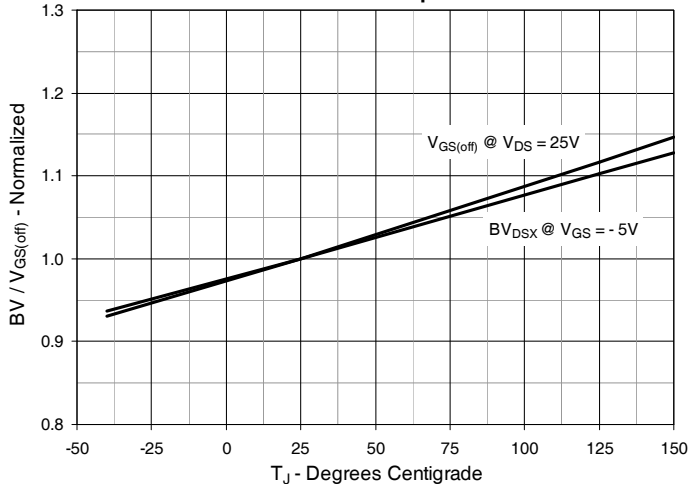
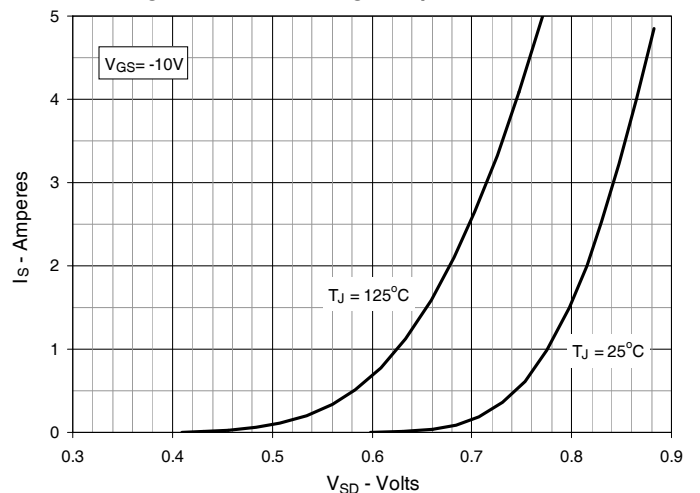
Fig. 7. Normalized $R_{DS(on)}$ vs. Junction Temperature

Fig. 8. $R_{DS(on)}$ Normalized to $I_D = 0.8A$ Value vs. Drain Current

Fig. 9. Input Admittance

Fig. 10. Transconductance

Fig. 11. Breakdown and Threshold Voltages vs. Junction Temperature

Fig. 12. Forward Voltage Drop of Intrinsic Diode


Fig. 13. Capacitance

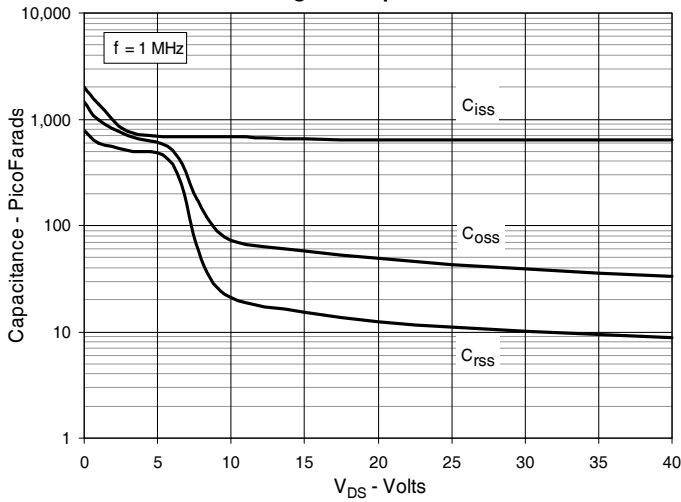


Fig. 14. Gate Charge

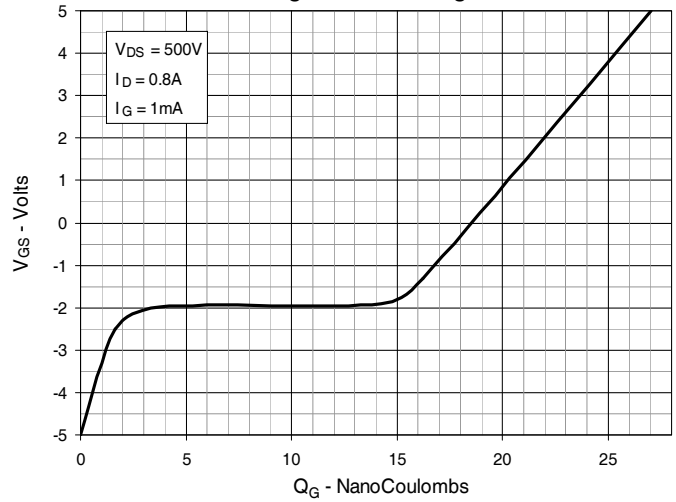


Fig. 15. Forward-Bias Safe Operating Area @ $T_C = 25^\circ\text{C}$

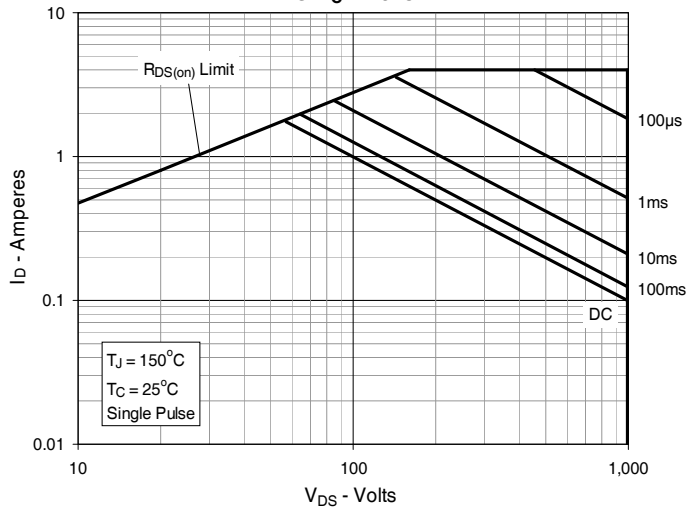


Fig. 16. Forward-Bias Safe Operating Area @ $T_C = 75^\circ\text{C}$

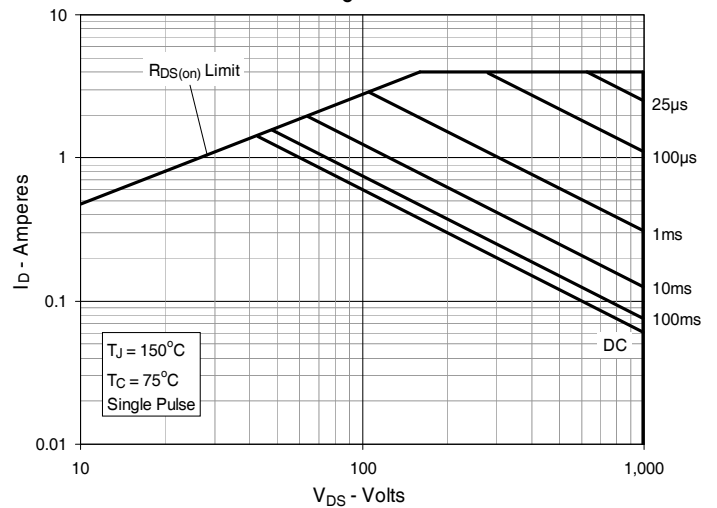
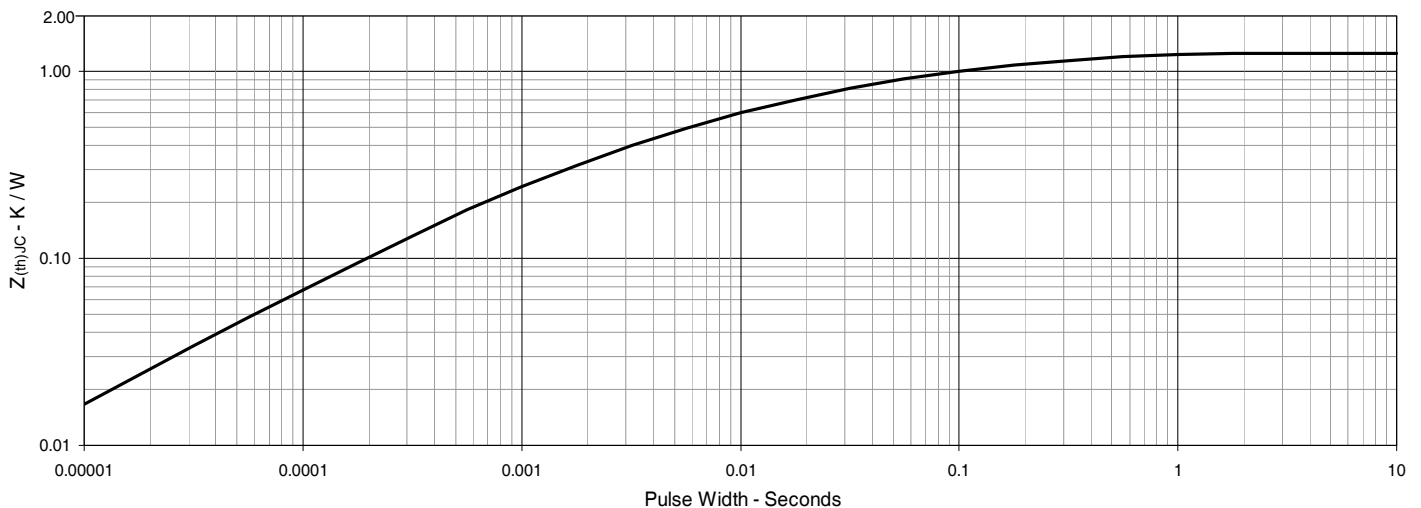
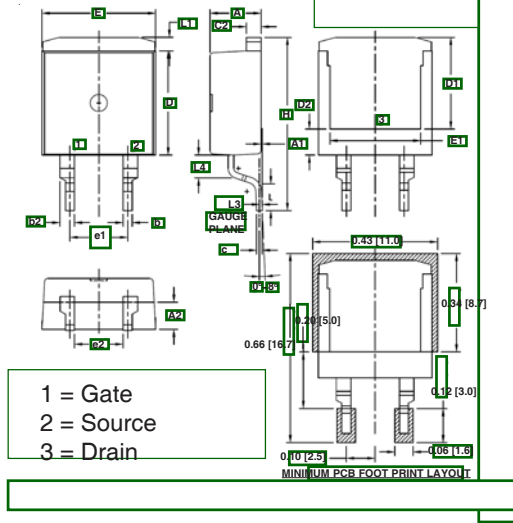


Fig. 17. Maximum Transient Thermal Impedance



TO-263HV Outline


| SYM | INCHES | | MILLIMETER | |
|------|----------|------|------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .170 | .185 | 4.30 | 4.70 |
| A1 | .000 | .008 | 0.00 | 0.20 |
| A2 | .091 | .098 | 2.30 | 2.50 |
| b | .028 | .035 | 0.70 | 0.90 |
| b2 | .046 | .054 | 1.18 | 1.38 |
| C | .018 | .024 | 0.45 | 0.60 |
| C2 | .049 | .055 | 1.25 | 1.40 |
| D | .354 | .370 | 9.00 | 9.40 |
| D1 | .311 | .327 | 7.90 | 8.30 |
| D2 | .083 | .098 | 2.10 | 2.50 |
| E | .386 | .402 | 9.80 | 10.20 |
| E1 | .307 | .323 | 7.80 | 8.20 |
| e1 | .200 BSC | | 5.08 BSC | |
| (e2) | .163 | .174 | 4.13 | 4.43 |
| H | .591 | .614 | 15.00 | 15.60 |
| L | .079 | .102 | 2.00 | 2.60 |
| L1 | .039 | .055 | 1.00 | 1.40 |
| L3 | .010 BSC | | 0.254 BSC | |
| (L4) | .071 | .087 | 1.80 | 2.20 |



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